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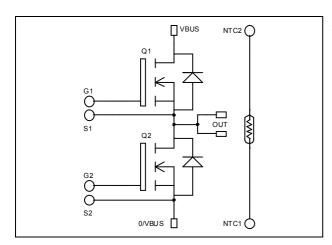






Phase leg MOSFET Power Module

$$\begin{split} V_{DSS} &= 500 V \\ R_{DSon} &= 38 m \Omega \text{ typ } @ \text{ Tj} = 25^{\circ} C \\ I_D &= 90 A @ \text{ Tc} = 25^{\circ} C \end{split}$$



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O/VBUS

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

VBUS

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		500	V
I_D	Continuous Drain Current	$T_c = 25$ °C	90	
1D	Continuous Diani Current	$T_c = 80$ °C	67	A
I_{DM}	Pulsed Drain current		360	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		45	mΩ
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		694	W
I_{AR}	Avalanche current (repetitive and non repetitive)		46	A
E _{AR}	Repetitive Avalanche Energy		50	mJ
E_{AS}	Single Pulse Avalanche Energy		2500	1113

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$	$T_j = 25^{\circ}C$			200	4	
		$V_{GS} = 0V, V_{DS} = 400V$	$T_j = 125$ °C			1000	μΑ	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 45A$			38	45	mΩ	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$		3		5	V	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{V}$				±150	nA	

Dynamic Characteristics

•	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		11.2		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		2.4		nF
C_{rss}	Reverse Transfer Capacitance	f=1MHz		0.18		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		246		
Q_{gs}	Gate – Source Charge	$V_{\text{Bus}} = 250V$		66		nC
Q_{gd}	Gate – Drain Charge	$I_D = 90A$		130		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		18		
$T_{\rm r}$	Rise Time	$V_{GS} = 15V$ $V_{GS} = 232V$		35		
$T_{d(off)}$	Turn-off Delay Time	$\begin{aligned} V_{Bus} &= 333V \\ I_D &= 90A \\ R_G &= 2\Omega \end{aligned}$		87		ns
T_{f}	Fall Time			77		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V$, $V_{Bus} = 333V$ $I_D = 90A$, $R_G = 2\Omega$		1510		т
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy			1452		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 90A, R_G = 2\Omega$		2482		
E _{off}	Turn-off Switching Energy			1692		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{S}	Continuous Source current		$Tc = 25^{\circ}C$			90	Α
ıs	(Body diode)		$Tc = 80^{\circ}C$			67	А
$ m V_{SD}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -90A$	L			1.3	V
dv/dt	Peak Diode Recovery •					15	V/ns
4	Reverse Recovery Time		$T_j = 25^{\circ}C$		233		
t_{rr}		$I_S = -90A$ $V_R = 333V$	$T_j = 125$ °C		499		ns
Q _{rr}	Reverse Recovery Charge	$di_{S}/dt = 200A/\mu s$	$T_j = 25^{\circ}C$		3.8		μC
			$T_j = 125$ °C		11.4		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \le -90A$ $di/dt \le 700A/\mu s$ $V_R \le V_{DSS}$ $T_i \le 150$ °C

Thermal and package characteristics

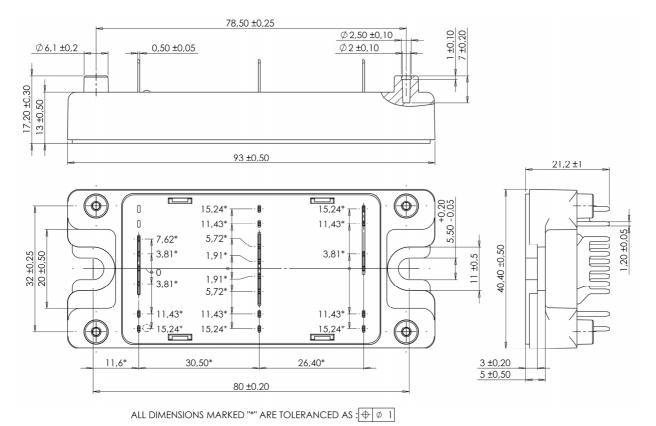
Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance					0.18	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature at T

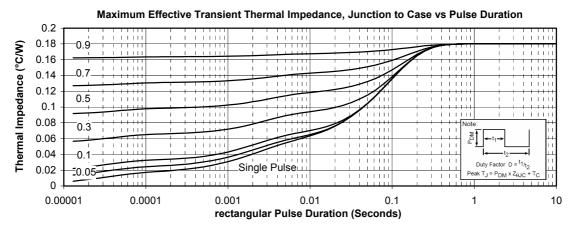
SP4 Package outline (dimensions in mm)

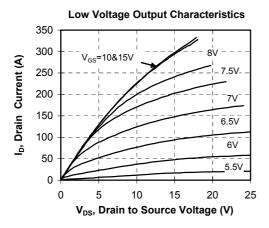


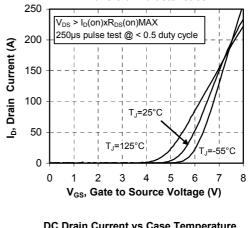
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com



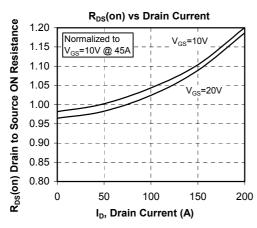
Typical Performance Curve

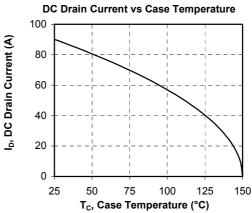




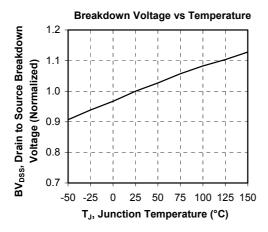


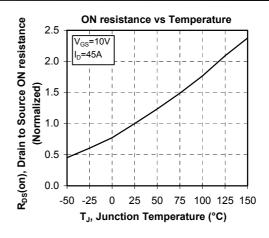
Transfert Characteristics

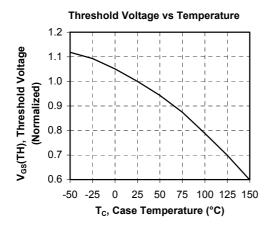


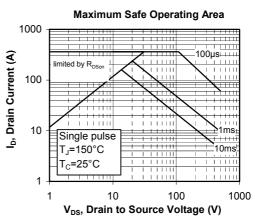


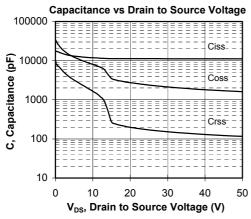


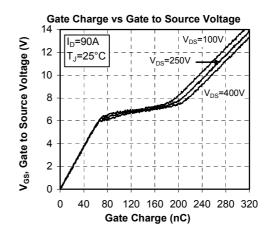








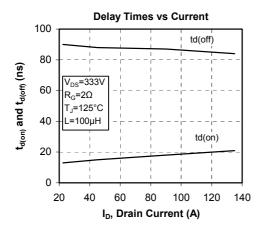


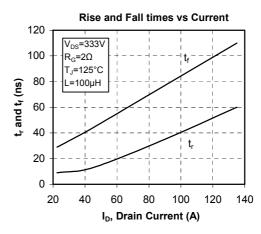


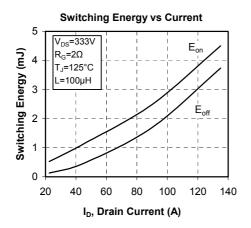
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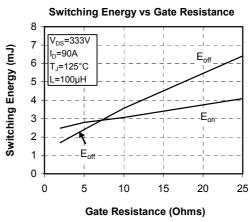
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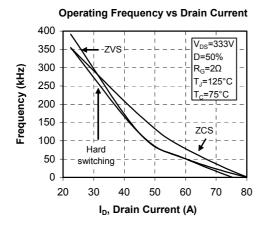


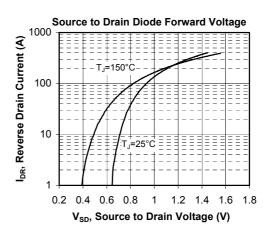














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